



BESIII



CGEM ASIC GENERAL

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14-April-2016, Turin

BESIII CGEM FEE/DAQ/Trigger Workshop

Design Team

- Designers (**Analog Front-end**):
 - H. S. Li (IHEP, INFN)
 - C. Y. Leng (INFN, IHEP)
 - J. Y. Chai (INFN, IHEP)
- Technical Advisors:
 - A. Rivetti (INFN)
 - M. Rolo (INFN)

CGEM FEE

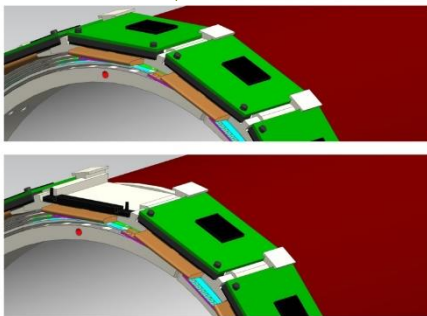
- **Goals**
 - Spatial Resolution $\sim 120 \mu\text{m}$
 - Time Resolution of the order of $4\text{-}5\text{ns}$
 - Short Dead Time $< 1\mu\text{s}$ (shaping time+analog-to-digital conversion time) to limit Pile-up probability at a few %
- **Channels**
 - $\sim 10\ 000$ Channels $\rightarrow 160$ ASICs $\rightarrow 80$ PCB
 - 64 Channels per ASIC $\rightarrow 2$ ASICs per PCB
- **ASIC Requirements**
 - $1 - 50$ fC Input Charge
 - Up to 100 pF Sensor Capacitance
 - 60 kHz Rate per Channel (safety factor of 4 included)
- **Trigger Latency $6.4 \mu\text{s}$**

FEE BLOCK DIAGRAM

ON-DETECTOR ELECTRONICS
~ 10 000 CHANNELS



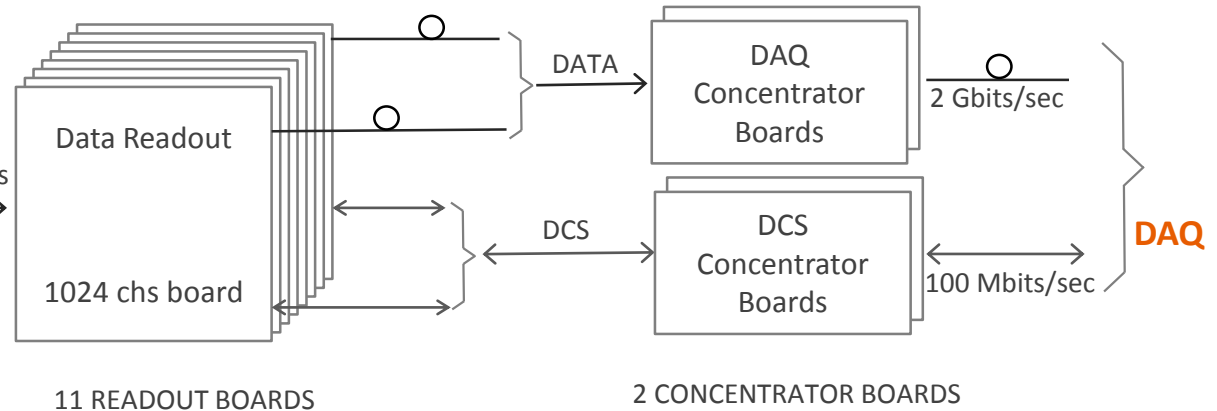
160 ASIC -> 80 BOARDS



INFN-TORINO
IHEP-China

Turin, 14-April-2016

OFF-DETECTOR ELECTRONICS



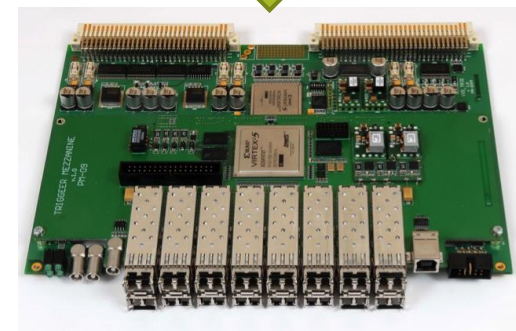
11 READOUT BOARDS

2 CONCENTRATOR BOARDS



INFN-FERRARA

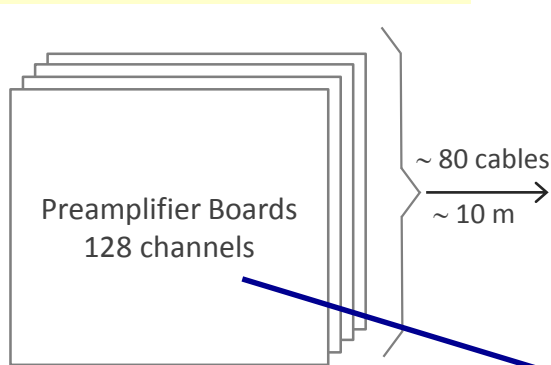
INFN-LNF



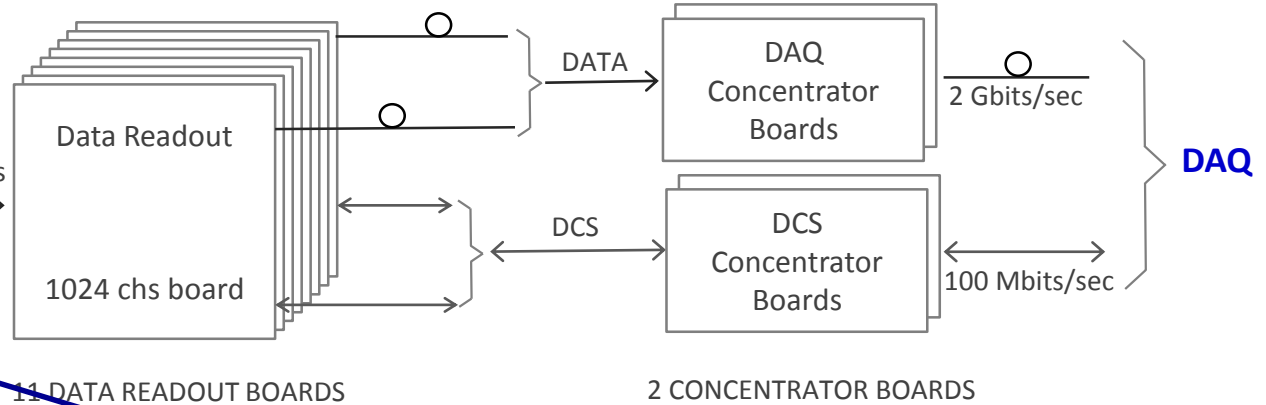
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FEE BLOCK DIAGRAM

ON-DETECTOR ELECTRONICS
~ 10 000 CHANNELS



OFF-DETECTOR ELECTRONICS

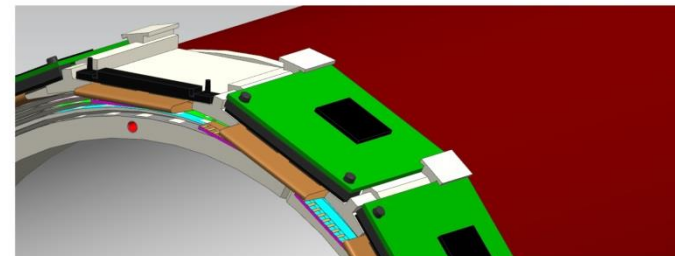
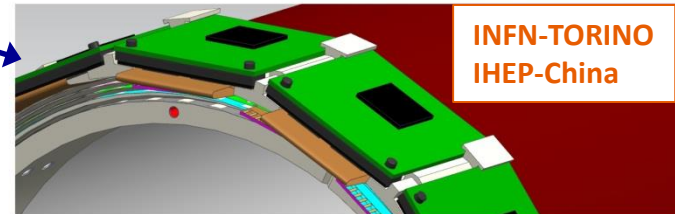


GEM LAYERS

- I 32 ASICs 16 PCB
- II 56 ASICs 28 PCB
- III 72 ASICs 36 PCB

NUMBERS

- 64 Channels per ASIC
- 1 PCB → 2 ASICs
- 10 240 Ch → 80 PCB



CGEM ASIC



CGEM ASIC under development at **INFN-Torino** in Collaboration with **IHEP**, which provides two PhD students(2x3 years) and one Expert (2 years) for ASIC design and tests , with two technical advisors (**A. Rivetti and M. Rolo**)

Design started from **TOFPET ASIC** and **TOFPET2 ASIC**

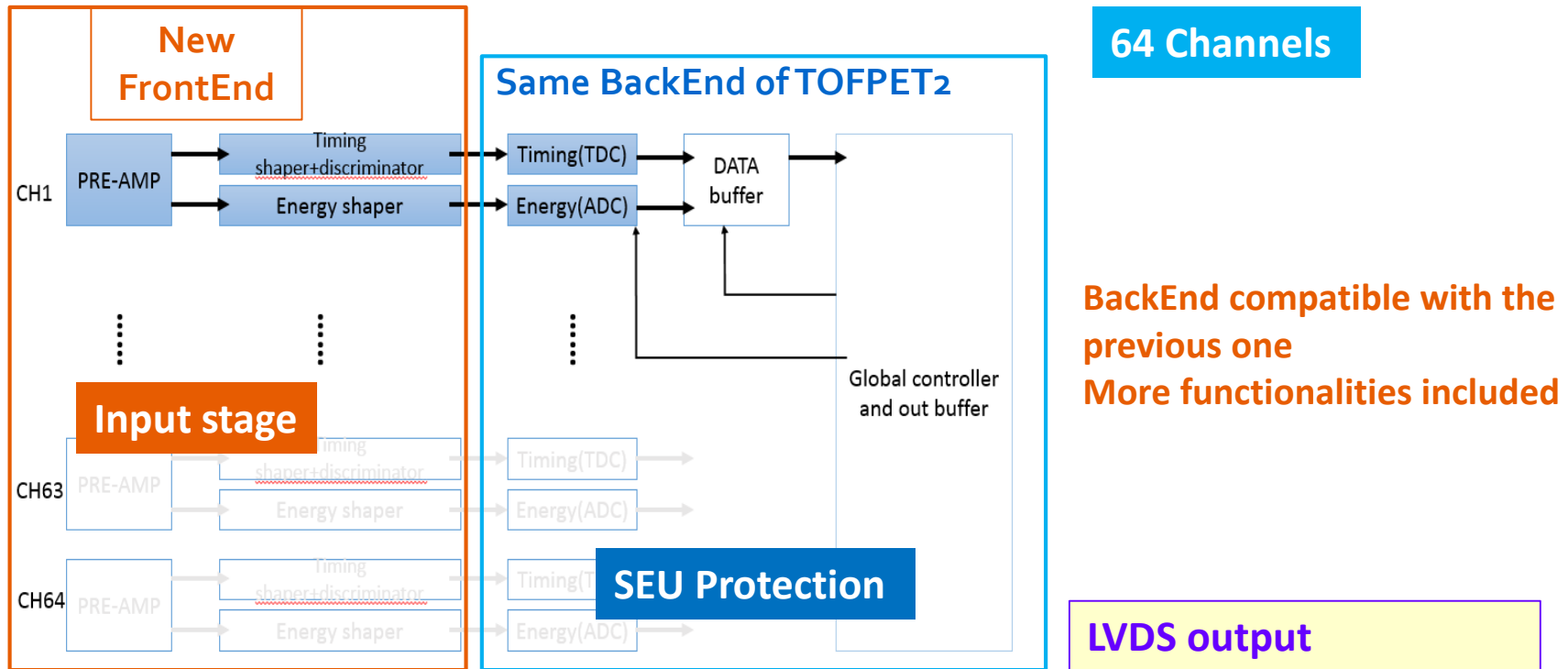
➤ **TOFPET** used for Medical PET Applications ,
IBM 130nm, (TOFPET2 UMC110nm)
no SEU protection, FEE suitable for SiPM signals



➤ **CGEM-ASIC** developed for **BESIII** experiment,
UMC 110nm (exportable in China, limited power consumption,
reduced cost wrt IBM, to be tested for Radiation Tolerance),
SEU protection, FEE suitable for GEM signals

-Time and charge measurements by TDC and ADC *About TOFPET ASIC, Please see M. Rolo 's slides*
-Digital output

Overview of the channel architecture **after** August 2015

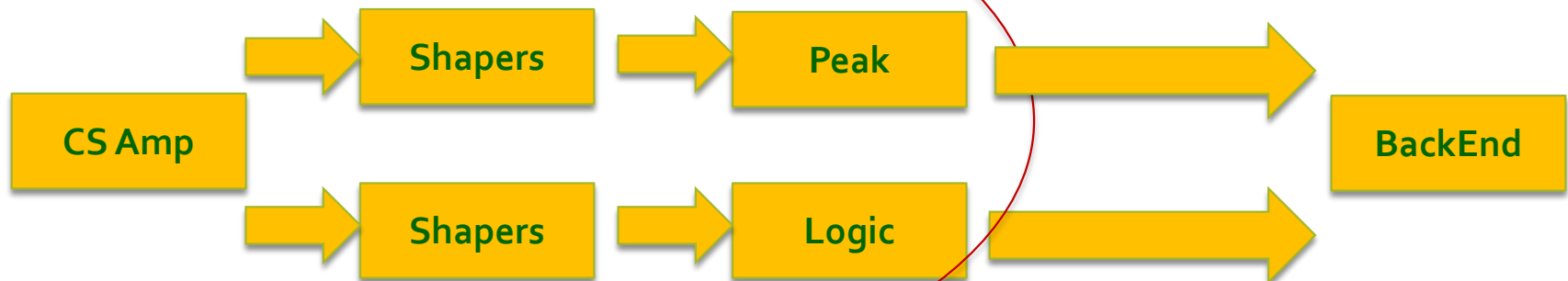


- **TOFPET2 BackEnd, developed for PET application, will be used instead**
 - **UMC 110 nm**
 - **Charge is measured by an ADC**
 - **SEU protection has been implemented**

PREAMP AND SHAPER

- Based on PMOS input transistors

Slower shapers for charge measurement

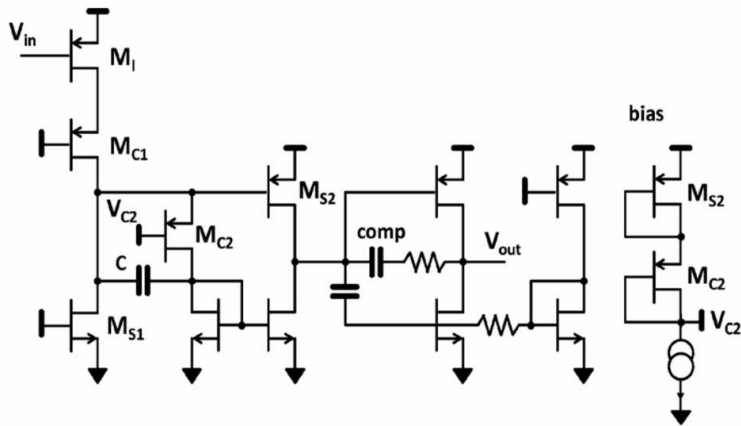


Fast signal for time measurement

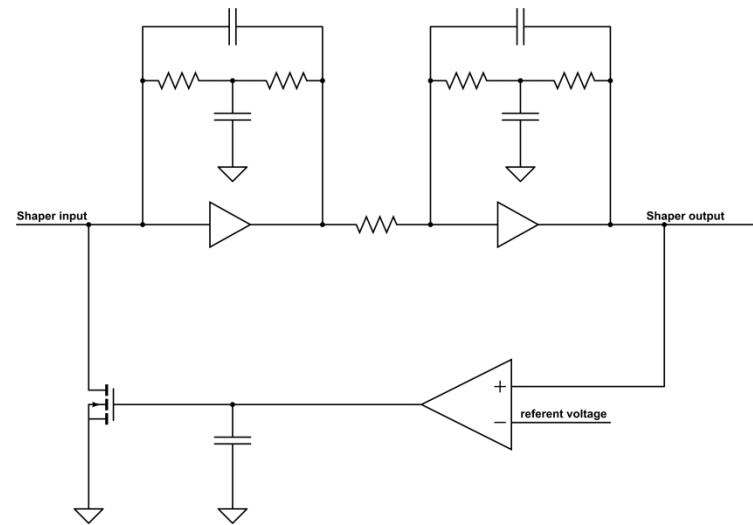
Detector capacitance: up to 100pF

- Noise performance related to the adjustable peaking time:
<700e- @200ns
- Timing performance 5.5 ns@1fC input, 100pF
- Power consumption \approx 5mW (Preamp+shaper) + 4mW (digital part) total < 10mW
- Full signal pulse width (energy branch) \approx 900ns
- Output gain (energy branch) \approx 12mV/fC

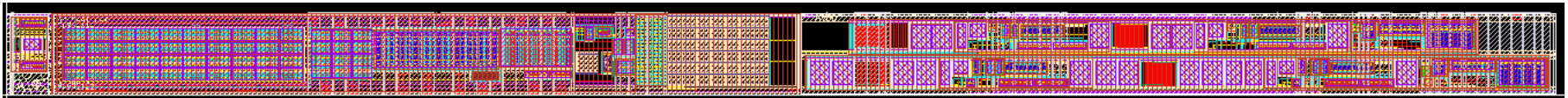
Preamplifier and shape



Core of the pre-amplifier



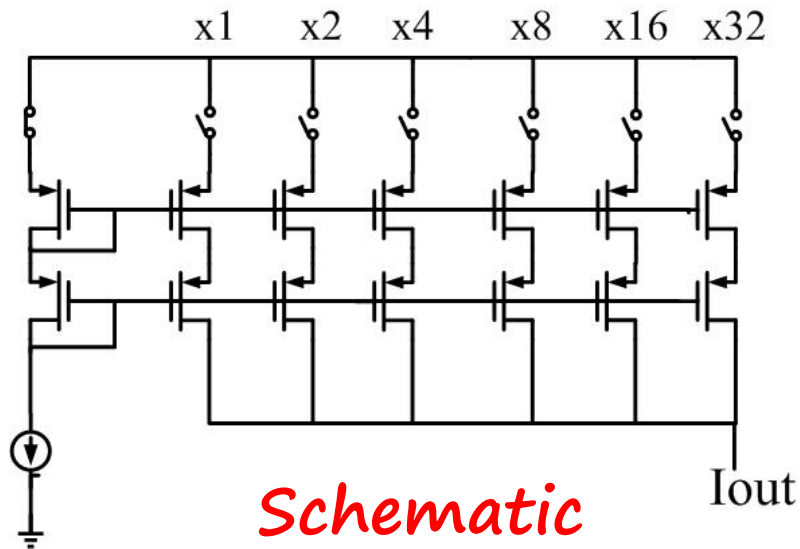
shaper



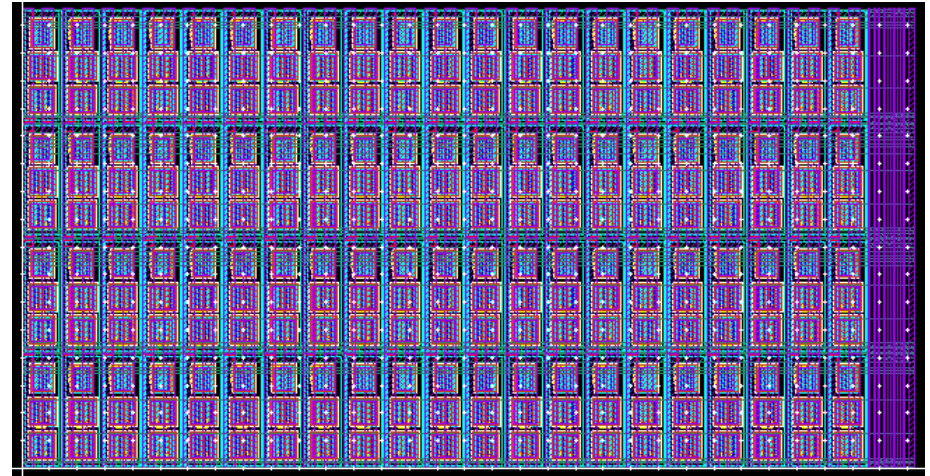
Layout of one channel of the preamplifier and shaper : $72 \mu\text{m} \times 1350 \mu\text{m}$

Details of the front-end, please see Chongyang's slides

6bit DACs design



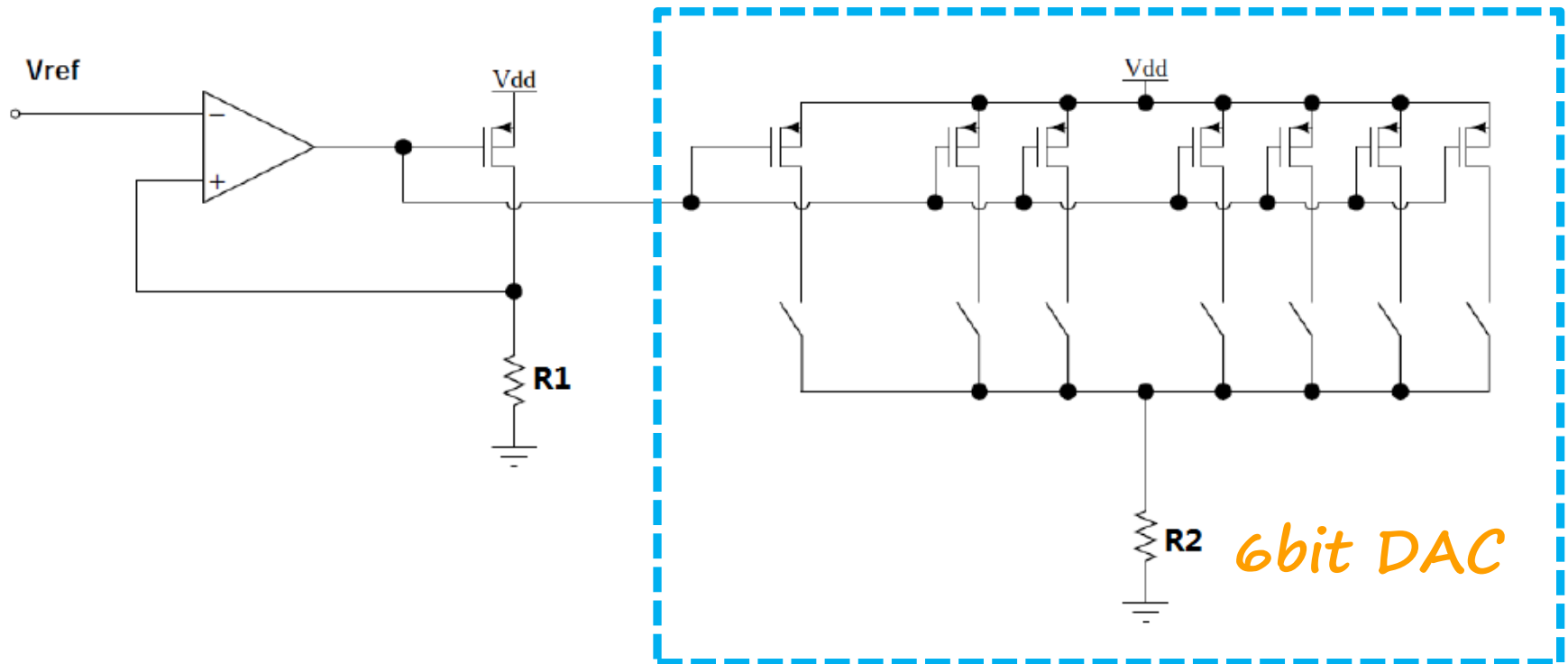
Schematic



Layout

- Only for **the bias**, no demand of speed
- **LSB=3.6uA**
- **Output: 0V → 0.7V (64LSB@3kΩ)**
- **Area: 160um x 80um**

Bias circuit



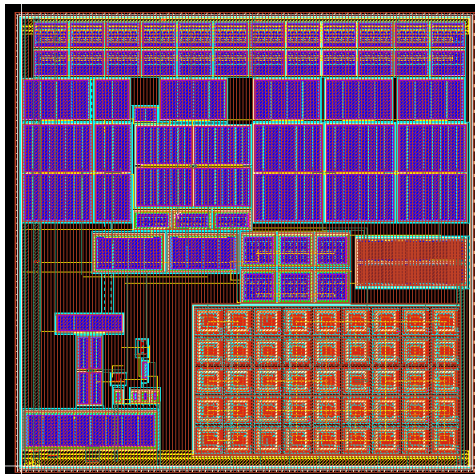
Some analog parameters of the preamplifier need to be finely tuned for the optimized performance

Bandgap Design

To get a temperature and power supply independent voltage reference.

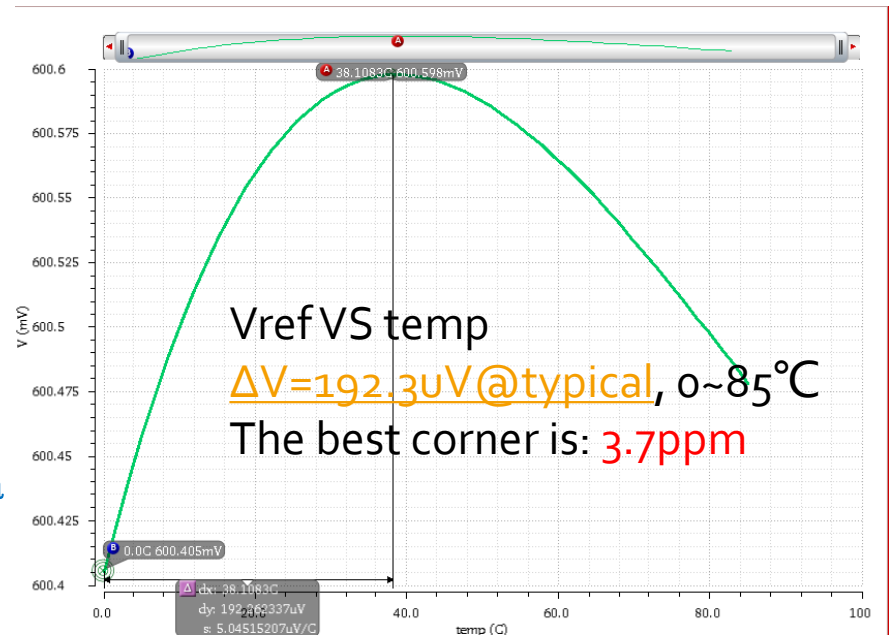
To generate a precise references for the chip.

This Bandgap IP is ready to be used in a second version



Area: 300um * 300um, Power: 250uA

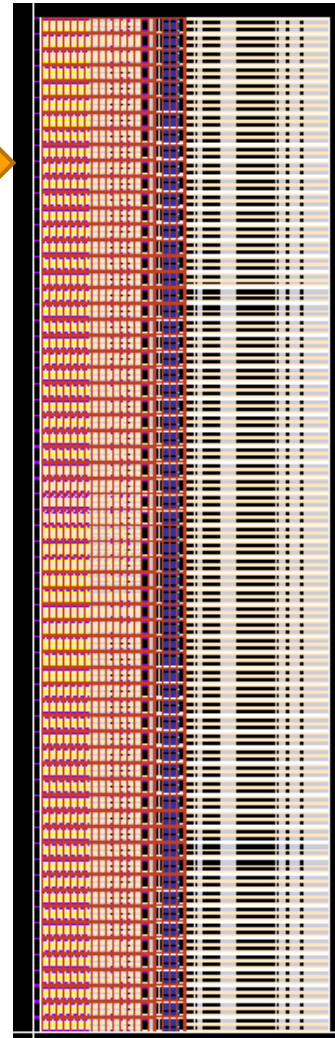
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- $V_{REF} = 601.4 \text{ mV} @ 27^\circ C$ Typical
- $V_{supply_min} = 1.0 \text{ V}$
- Temperature coefficient: 3.77ppm/°C
- $\Delta V_{out} / \Delta V_{supply} = 6.8 \text{ mV/V}$
- $\Delta V_{out} / \Delta T = 0.03 \text{ mV} / ^\circ C$
- Power = 0.3mW
- Area: 300X300 μm^2
- RMS Noise: 44 μV

Layout of the Front-end

- 64-channel pre-amplifier and shaper is OK
- Power Grid finished
- Post simulation shows it works well
- Bias layout design is ongoing



Summary

- Front-end
 - The 64-channel layout finished
 - Post simulation results are good
 - Some layout needs to be modified for fitting the back-end
- Back-end
 - SEU protection included
 - Some reset function included
 - Ready for integration
- Submit at the beginning of May, 2016

Thank you!